Molecular Beam Epitaxy Growth of $InAs_{1-x}Bi_x$ on GaSb for Topological Insulating States

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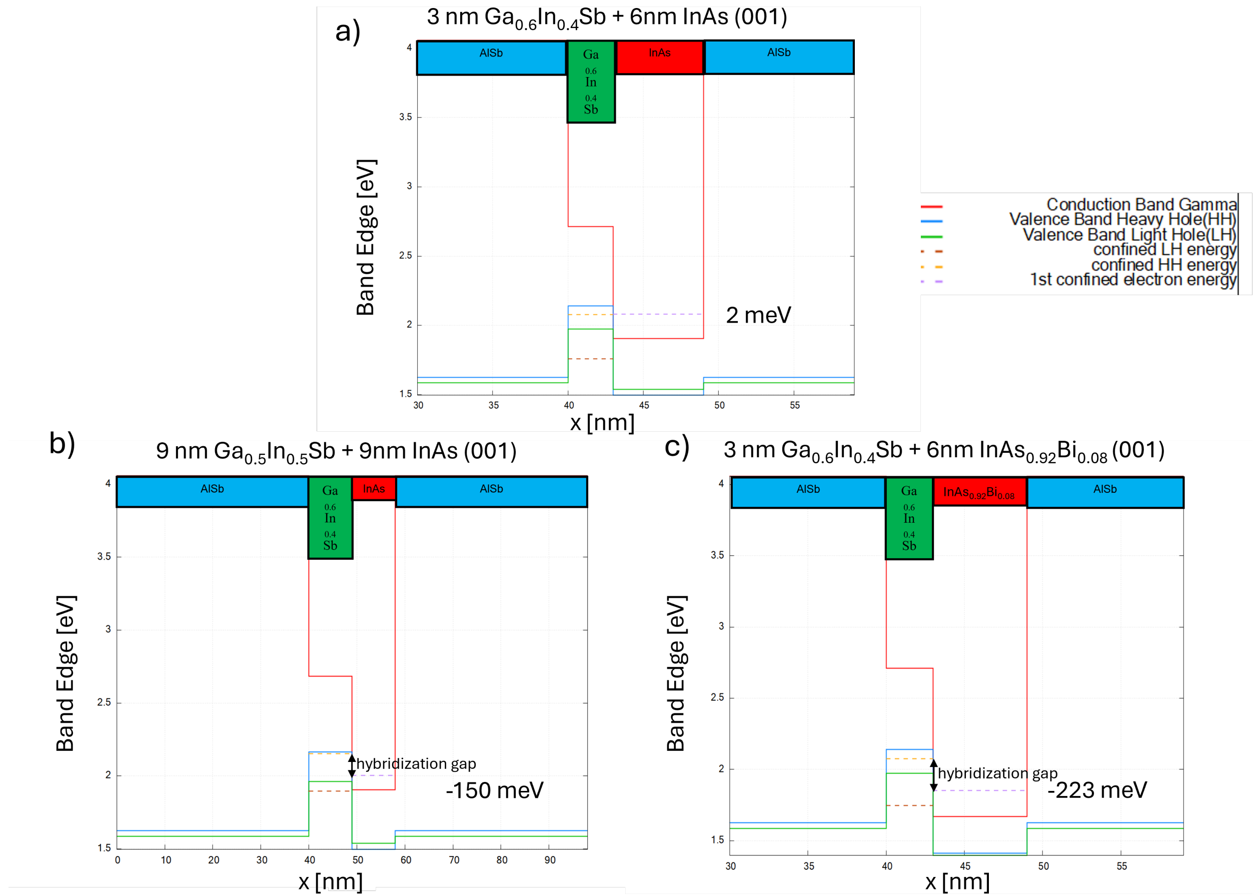

FIG. 1. **Band Edge diagrams of GaInSb/InAs(Bi) Quantum Well structures** a) 3 nm $Ga_{0.6}In_{0.4}Sb$ + 6nm InAs along (001) direction has 2 meV hybridization gap. b) 9 nm $Ga_{0.5}In_{0.5}Sb$ + 9nm InAs (001) with -150 meV hybridization gap. c) $Ga_{0.6}In_{0.4}Sb$ + 6nm $InAs_{0.92}Bi_{0.08}$ (001) with -223 meV hybridization gap.